ABSTRACT OF THE DISCLOSURE

Disclosed is a method for producing an HTSC band (16) on a substrate band (12), for example, a strong bond being created between the substrate band (12) and the band (16) as a result of the production process (e.g. PVD process or to the invention, According deposition). galvanic separation of the highly adhesive band (16)from the substrate band (12) is aided by the fact that the substrate band (12) is made of a shape memory alloy, the shape memory of the band being activated in a separating device (15) by means of heating and, possibly, cooling. Tension-related stress is generated in the joint on the boundary surface between the bands (12, 16) as a result of the substrate being deformed such that separation of the band (16) from the substrate band (12) is aided or even caused. disclosed is a production facility in which the substrate band is made of a shape memory alloy.